



## Power Electronics and Motor Drive Technologies for Automobile Electrification



[https://www.nissan-global.com/JP/TECHNOLOGY/OVERVIEW/e\\_powertrain.html](https://www.nissan-global.com/JP/TECHNOLOGY/OVERVIEW/e_powertrain.html)

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Prof. Keiichiro Kondo

## Power Electronics(PE) and Motor Drive(MD) Technologies for Automobile Electrification

1. Introduction
2. Expectation to SiC-MOSFET.
3. Technologies for high power motor drive system
4. Conclusions

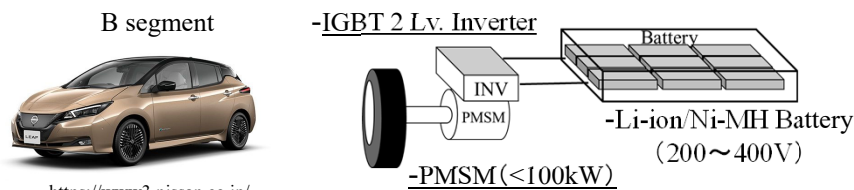
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## Once typical design of electric traction system



## Recent requirement for EV

Market	B segment, C segment...Commercial Vehicle
Motor power	Expand to more than 100kW
Battery voltage	Expand to 800V

## More recent design for traction system

Motor : PMSM, IM, WFSM...  
Inverter : 2Lv, 3Lv...IGBT, SiC-MOSFET, GaN-MOSFET...

What is better design?

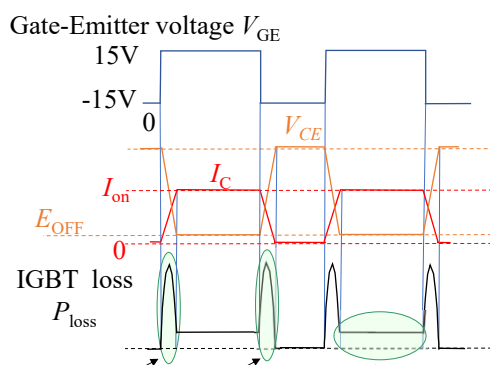
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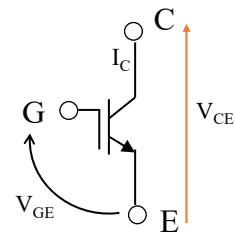
## Loss of power semiconductor devices

Example : IGBT



**switching loss**  
loss with transient current and voltage

**conduction loss**  
loss with steady current and forward voltage



cooling fin for power devices

<https://www.spp.co.jp/netsu/products/pdc/>

## SiC-MOSFET power semiconductor devices

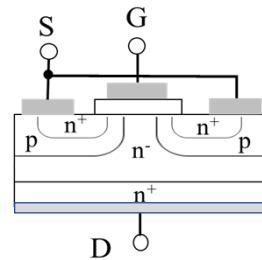
### Benefit of Power MOS-FET

- High speed switching  
(No tail current)

### Draw back due to Unipolar device

#### High conduction resistance

→ Lower voltage application (Less than 800V by Si device))



### Wide Band Gap semiconductor (SiC)

Down sized DC/DC converter and traction inverter  
with SiC-MOSFET

## Property of SiC-MOSFET power semiconductor devices

### 600V Si IGBT vs. 600V MOSFET

	Si-MOSFET	Si-IGBT	SiC-MOSFET
on loss	1	0.1	0.01
switching loss	1	10	1
switching duration	1	5 - 10	1
switching frequency	1	0.05 - 0.1	1
operating temp.	1	1	1.5 - 2.0

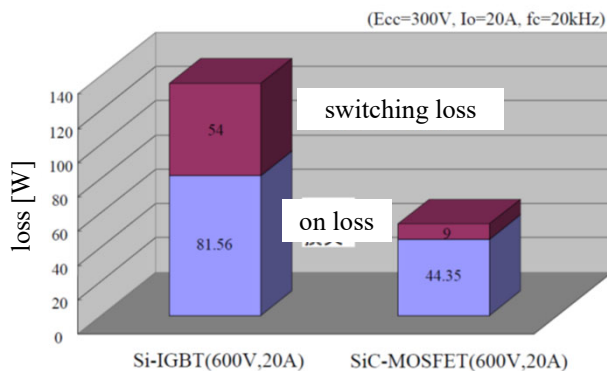
<http://www.iae.or.jp/PROJECT/nws/pdf/d2/s6.pdf>

### Wide band gap

Less loss and higher connection surface temperature

### Property of inverter loss

#### loss comparison in 2 kW class inverter



<http://www.iae.or.jp/PROJECT/nws/pdf/d2/s6.pdf>

#### Loss of SiC MOSFET 2 kW inverter

50% less loss than IGBT inverter 9

### Conduction loss of 3.3 kV SiC-MOSFET vs 3.3 kV Si-IGBT

SiC-MOSFET → 1/3 conduction loss @800A of Si IGBT

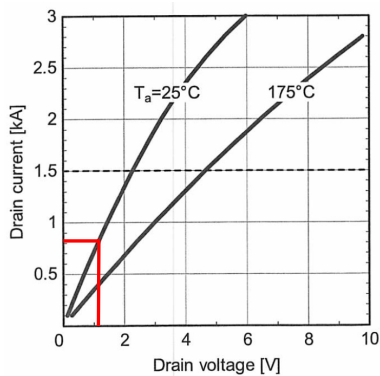
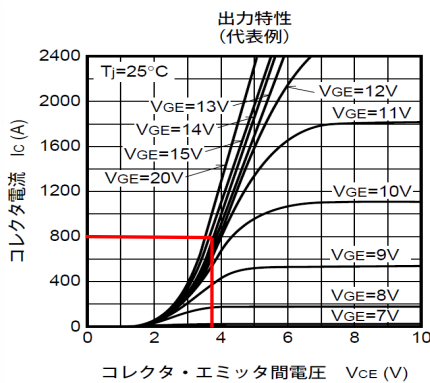


Figure 2.  $I_{DS}-V_{DS}$  characteristics of a 3.3 kV all-SiC traction inverter module.

#### 3.3kV SiC-MOSFET



#### 3.3kV Si-IGBT

IGBT: MELCO IGBT module CM1200HA-66H date sheet

MOSFET: M.Furuhashi et al "Practical Application of SiC-MOSFETs and further development" 10 Semiconductor Science and Technology 31 (2016) 034003, 9P

### Switching loss of 3.3 kV SiC-MOSFET vs 3.3 kV Si-IGBT

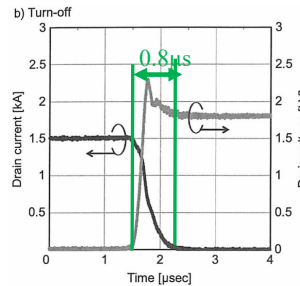
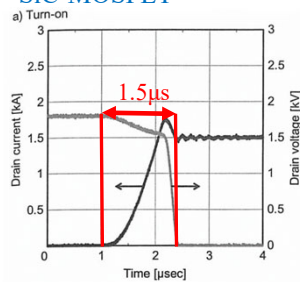
SiC-MOSFET → Less than 1/3 switching loss of Si IGBT

#### 3.3kV Si-IGBT

td (on)	turn on delay time	VCC = 1650V, IC = 1200A	1.60	μs
tr	turn on rise time	VGE1 = VGE2 = 15V	2.00	μs
td (off)	turn off delay time	RG = 2.5Ω	2.50	μs
tf	turn off fall time	rheostatic load	1.00	μs

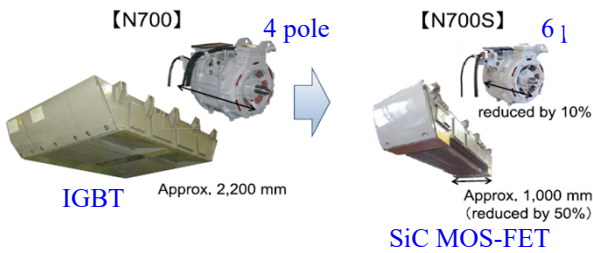
#### 3.3kV SiC-MOSFET

IGBT: MELCO IGBT module CM1200HA-66H date sheet



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### Example of down sized power converter for Shinkansen vehicle by 3.3kV SiC MOS-FET



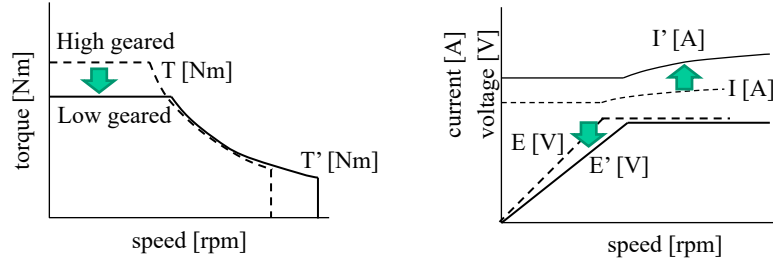
Cited to Nippon-syaryo web-site

Kenji Sato, Hirokazu Kato, Takafumi Fukushima, "Outstanding Technical Features of Traction System in N700S Shinkansen New Generation Standardized High Speed Train", Journal of Industrial Application of IEEJ, Vol.10 No.4 pp.402-410, 2021.3

#### Comparison mass of the traction systems

	Number per train	N700	N700S
Transformer	4	3600kg	3500kg
Power converter	14	1500kg(IGBT)	1000kg(SiC MOS-FET)
Traction motor (305kW)	56	approx. 400kg	approx. 350kg
All over Traction system		58t (100%)	47t (81%)

Expectation to SiC MOS-FET -Expanding the current region -



Changing N-T characteristics

Mechanical traction system  $\Rightarrow$  Changing Gear ratio  
 Electricals traction system  $\Rightarrow$  Changing current-voltage characteristics

SiC MOSFET

Easy to increase current : More freedom of N-T characteristics

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## Enhancing the DC input voltage1.

EV for C segment vehicle

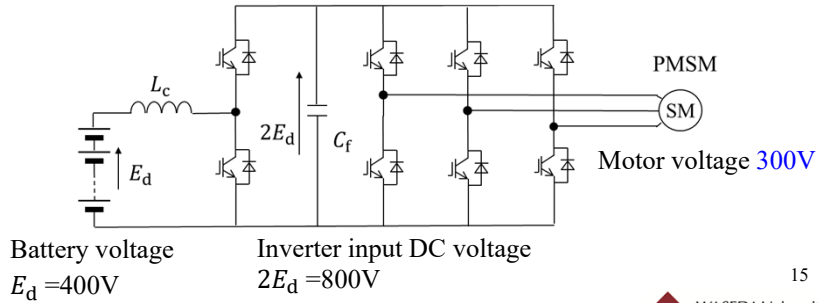
Motor voltage 150V → 300V



[https://www.subaru.jp/solterra/solterra/grade/index?view\\_menu](https://www.subaru.jp/solterra/solterra/grade/index?view_menu)

Conventional circuit configuration

DC/DC convert + IGBT 2 Level inverter



## Enhancing the DC input voltage2.

EV for C segment vehicle

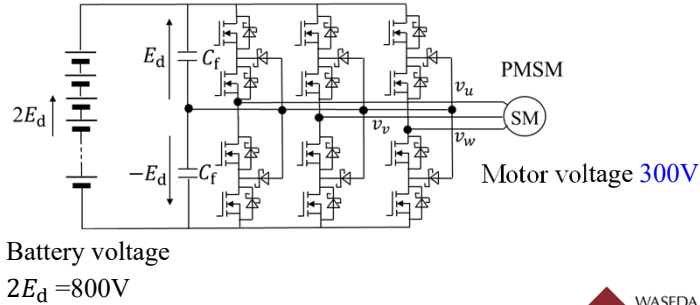
Motor voltage 150V → 300V



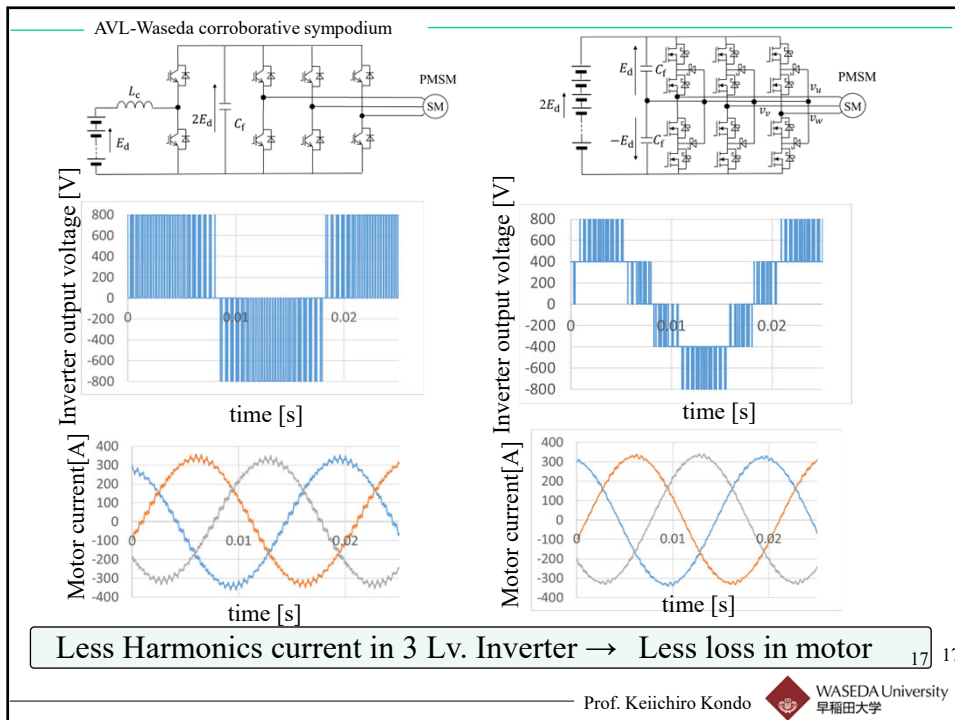
[https://www.subaru.jp/solterra/solterra/grade/index?view\\_menu](https://www.subaru.jp/solterra/solterra/grade/index?view_menu)

Higher battery voltage  
+ SiC MOSFET Level inverter

Less size and lower switching loss even more semiconductor devices







AVL-Waseda corroborative symposium

## Design of traction motor <https://ansys.oatnd.com/ntc-article-2-2>

Permanent magnet synchronous motor (PMSM)

- Highest efficiency
- Expensive permanent magnet
- Most applied traction motor type

Winding field synchronous motor (WFSM)

- wide speed operation range
- lotter lower efficiency than PMSM
- appropriate for part time operation

Induction motor (IM)

- lowest cost
- lower efficiency than PMSM
- appropriate for part time operation

Which is appropriate type of motor ?

Motor-CAD

図1 IPMSM設計の半径方向断面

Motor-CAD

図16 WFSM設計の半径方向断面

Motor-CAD

図10 IMの半径方向断面

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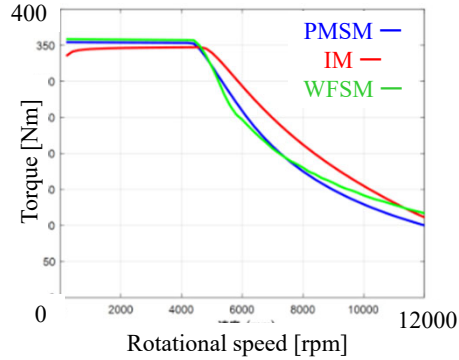
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## Design comparison of type of traction motor

Max Torque :350Nm  
 Max rotational speed :12000rpm  
 DC link volt. 400V  
 Max. current 500A(rms)  
 Outer size of stator: 250mm



[https://www.nissan-global.com/JP/TECHNOLOGY/OVERVIEW/e\\_powertrain.html](https://www.nissan-global.com/JP/TECHNOLOGY/OVERVIEW/e_powertrain.html)



N-T curve at max. torque performance

<https://ansys.oatnd.com/ntc-article-2-2>

160kW@max. class traction motor assumed

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## Design results 1 -PMSM-

Permanent magnet synchronous motor (PMSM)

### Design results

length of core[mm]:PMSM 100, IM 120, WFSM 120  
 over all length[mm]: PMSM 160, IM 200, WFSM 180  
 mass[kg]:PMSM 33.2, IM 47, WFSM 36.7

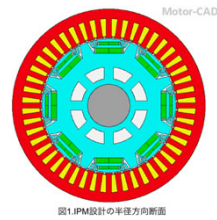
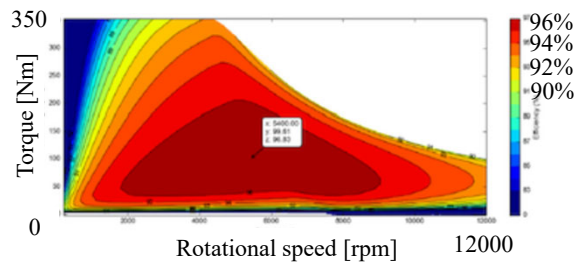


図1.PMSM設計の半径方向断面

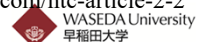
- Most down sized motor design
- High efficiency in the middle speed and partial load range.
- Appropriate for the town ride purpose.



efficiency map

<https://ansys.oatnd.com/ntc-article-2-2>

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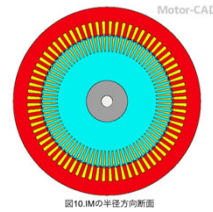


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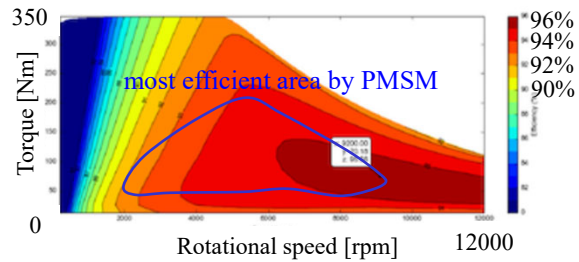
### Design results 2 -IM-

#### Induction motor (IM)

length of core[mm]:PMSM 100, **IM 120**, WFSM 120  
 over all length[mm]: PMSM 160, **IM 200**, WFSM 180  
 mass[kg]:PMSM 33.2, **IM 47**, WFSM 36.7



- Most bulky motor design.
- High efficiency in the high speed and right load range.
- Appropriate for the higher speed cursing.



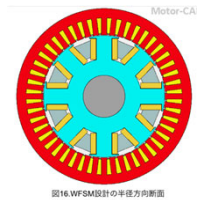
efficiency map

<https://ansys.oatnd.com/ntc-article-2-21>  
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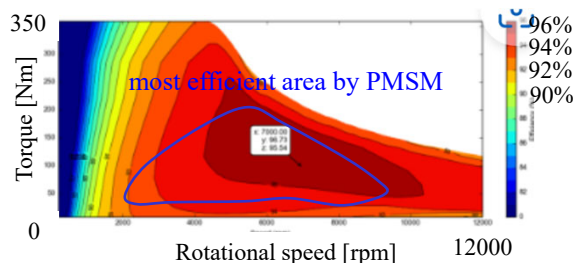
### Design results 3 -WFSM-

#### Winding field type synchronous motor (WFSM)

length of core[mm]:PMSM 100, IM 120, **WFSM 120**  
 over all length[mm]: PMSM 160, IM 200, **WFSM 180**  
 mass[kg]:PMSM 33.2, IM 47, **WFSM 36.7**



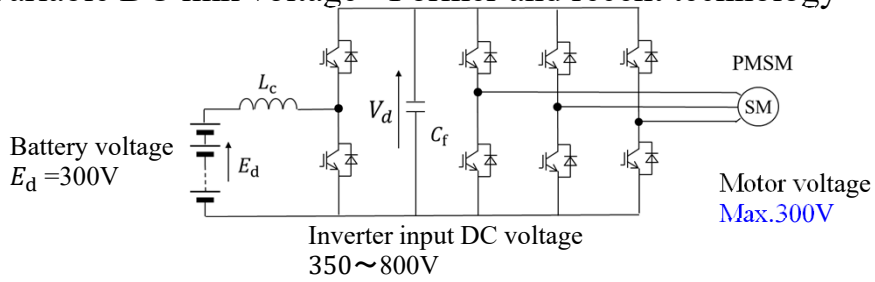
- Bulky motor design.
- High efficiency in the middle speed and middle load range.
- Appropriate for the suburban running.



efficiency map

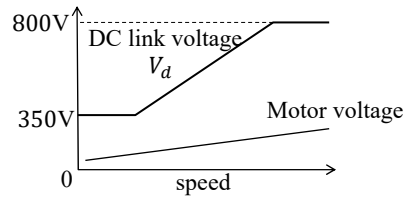
<https://ansys.oatnd.com/ntc-article-2-22>  
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## Variable DC link voltage -Former and recent technology-



### Former power devices

IGBT tale current loss reduced by variable DC link voltage.



### Recent power devices

-Less switching loss (ie: SiC-MOSFET) → Constant DC link voltage and higher switching  
 -Saving harmonics loss of motor

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## Summarizing today talk.

- Wide band gap device: Drastic less loss in power converter
- Type of traction motor : PMSM is not only choice!
- Inverter configuration : More choice along with the voltage and power

Appropriate Design is diversified along with the Market



<https://www3.nissan.co.jp/vehicles/new/leaf.html>



[https://www.tesla.com/ja\\_jp](https://www.tesla.com/ja_jp)



<https://press.siemens.com/global/en/feature/ehighway-solutions-electrified-road-freight-transport>

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Thank you for kind attention

